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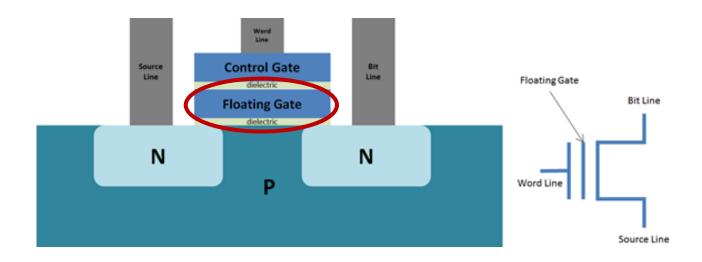
Fall 2024

Solid State Drives (SSDs)



Flash Memory Cell

- Transistor with floating gate
 - The floating gate is insulated all around with an oxide layer
 - Electrons trapped in the floating gate can remain for up to years



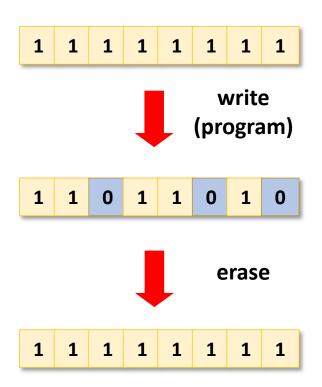
Flash Memory Characteristics

Erase-before-write

- Read
- Write or Program: $I \rightarrow 0$
- Erase: $0 \rightarrow 1$

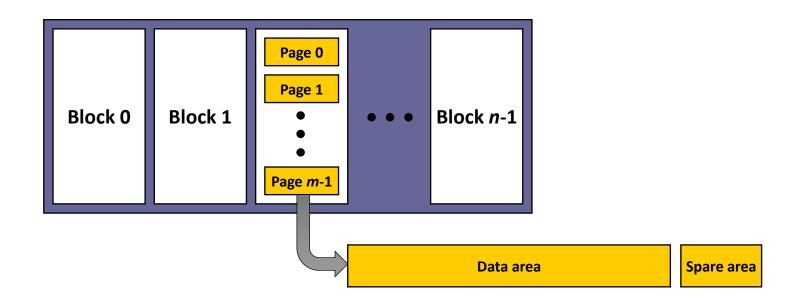
Bulk erase

- Program unit:
 - NOR: byte or word
 - NAND: page
- Erase unit:



Logical View of NAND Flash

- A collection of blocks
- Each block has a number of pages
- The size of a block or a page depends on the technology (but, it's getting larger)



NAND Flash Types

SLC NAND

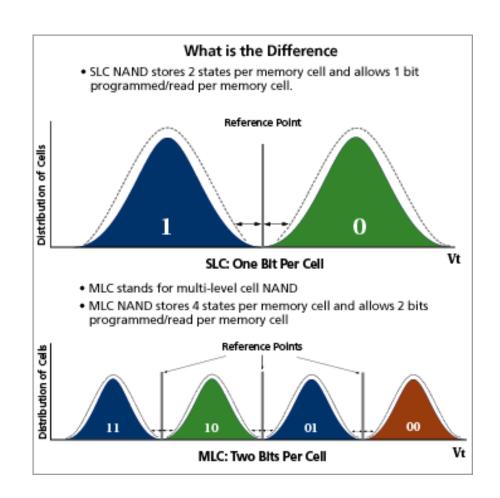
- Single Level Cell
- I bit/cell

MLC NAND

- Multi Level Cell (misnomer)
- 2 bits/cell

TLC NAND

- Triple Level Cell
- 3 bits/cell
- 3D NAND



NAND Applications

- Universal Flash Drives (UFDs)
- Flash cards
 - CompactFlash, MMC, SD, Memory stick, ...
- Smartphones
 - eMMC (Embedded MMC)
 - UFS (Universal Flash Storage)
- SSDs (Solid State Drives)
- Other embedded devices
 - MP3 players, Digital TVs, Set-top boxes, Car navigators, ...

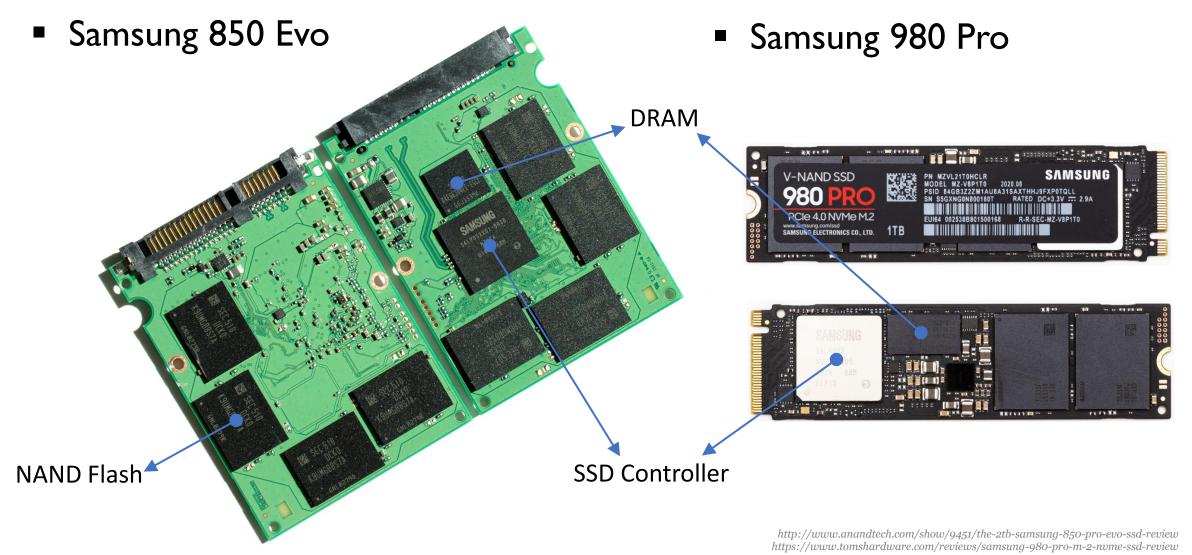




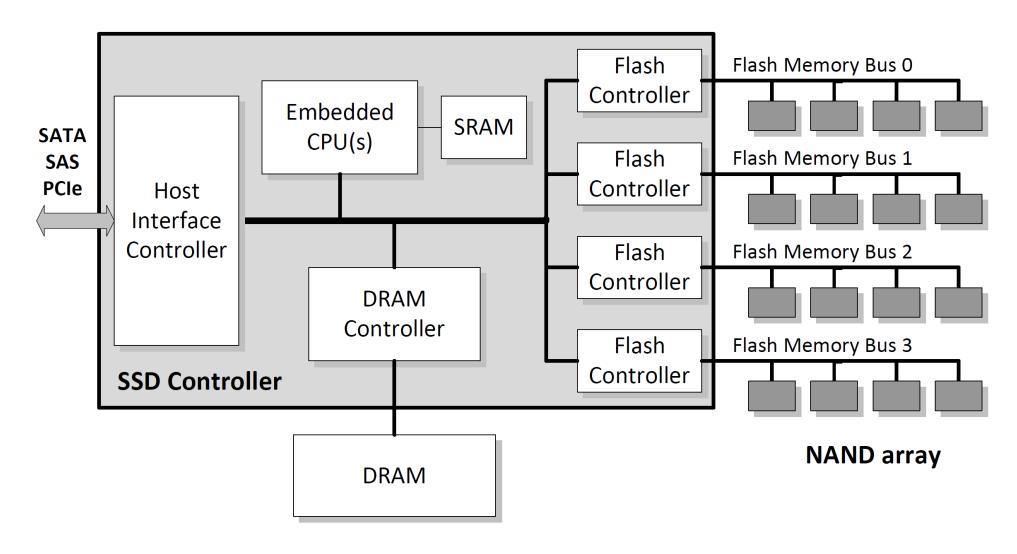




Anatomy of an SSD

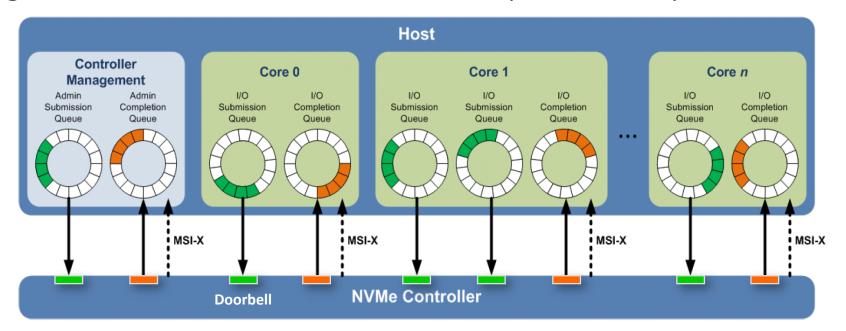


SSD Internals



NVMe SSD

- PCle-based (PCle Gen. 3: IGB/s per lane, up to 32 lanes)
- Deep queue: 64K commands per queue, up to 64K queues
- Streamlined command set: only 13 required commands
- One register write to issue a command ("doorbell")



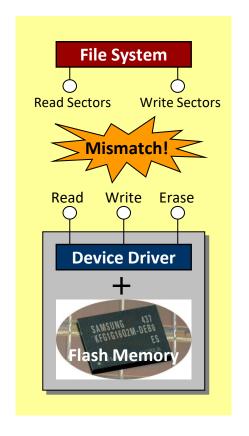
HDDs vs. SSDs

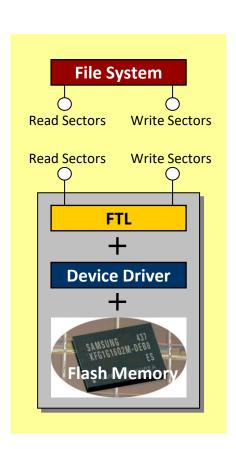
Feature	SSD (Samsung)	HDD (Seagate)			
Model	MZ-V8P2T0 (980 Pro)	ST2000LM003 (SpinPoint M9T)			
Capacity	2TB (512Gb 128-Layer 3D V-NAND TLC x 16 dies/chip x 2 chips)	2TB (3 Discs, 6 Heads, 5400 RPM)			
Form factor	M.2 (2280), 55g	2.5", 130g			
DRAM	2 GB	32 MB			
Host interface	NVMe (PCIe 4.0 x 4, 8GB/s)	SATA-3 (600 MB/s)			
Power consumption (Active / Idle / Sleep)	6.1 W/ 0.035 W / 0.005 W	2.3 W / 0.7 W / 0.18 W			
Performance	Sequential read: 7000 MB/s Sequential write: 5100 MB/s Random read: 1,000K IOPS (QD32) Random write: 1,000K IOPS (QD32) Random read: 22,000 IOPS (QD1) Random write: 60,000 IOPS (QD1)	Sequential read: 124 MB/s Sequential write: 124 MB/s Random read: 56 IOPS Random write: 98 IOPS Power-on to ready: 3.5 sec Average seek: 12/14 ms Average latency: 5.6 ms			
Price ¹	243,050 won (123won/GB)	66,000 won (33won/GB)			

¹ http://www.danawa.com (As of Nov. 29, 2023)

Flash Translation Layer (FTL)

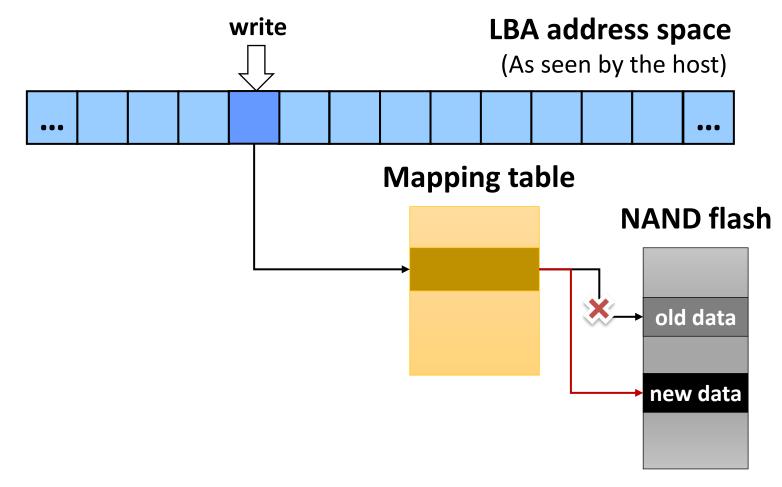
 A software layer to make NAND flash fully emulate traditional block devices (e.g., disks)





Address Mapping

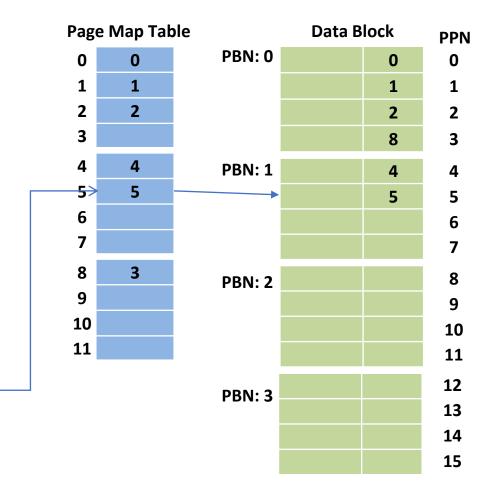
Required since flash pages cannot be overwritten



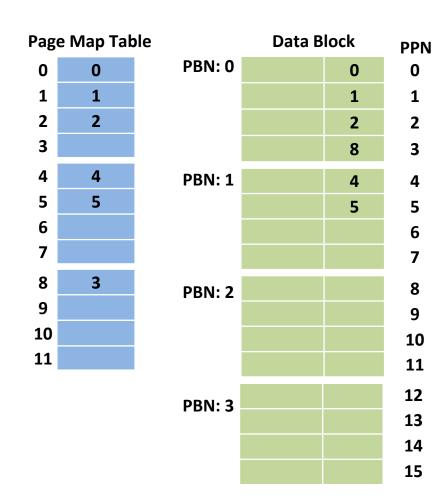
- Flash configuration
 - Page size: 4KB
 - # of pages / block = 4
- Current state
 - Written to page 0, 1, 2, 8, 4, 5
- Reading page 5

Logical page #5

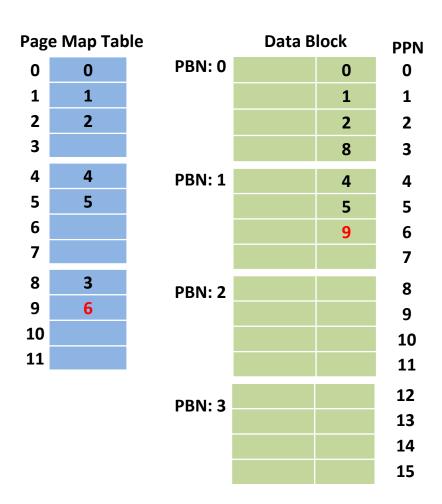
000000101



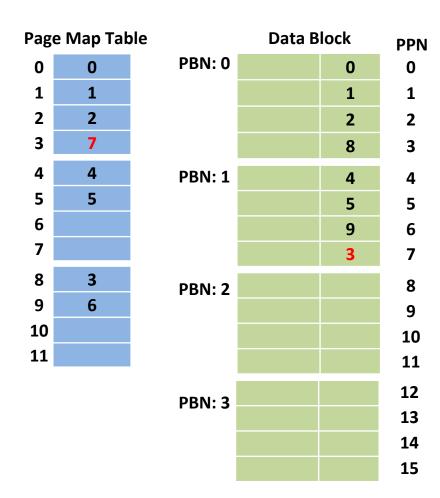
- Flash configuration
 - Page size: 4KB
 - # of pages / block = 4
- Current state
 - Written to page 0, 1, 2, 8, 4, 5
- New requests (in order)
 - Write to page 9
 - Write to page 3
 - Write to page 5



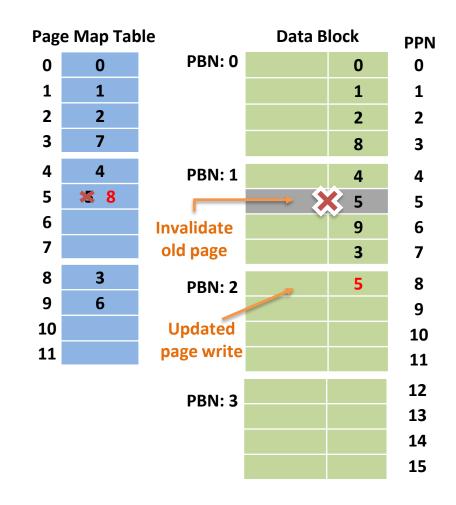
- Flash configuration
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 - Written to page 0, 1, 2, 8, 4, 5
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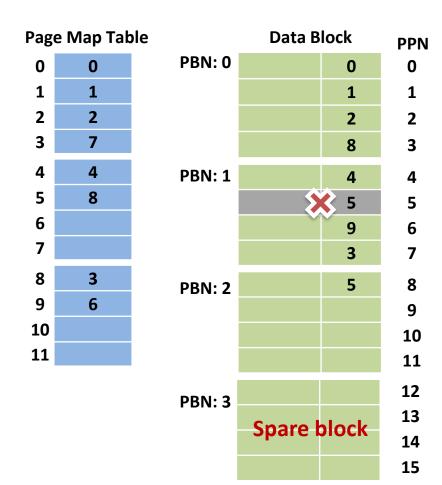
Garbage Collection

- Garbage collection (GC)
 - Eventually, FTL will run out of blocks to write to
 - GC must be performed to reclaim free space
 - Actual GC procedure depends on the mapping scheme
- GC in page-mapping FTL
 - Select victim block(s)
 - Copy all valid pages of victim block(s) to free block
 - Erase victim block(s)
 - Note: At least one free block should be reserved for GC

Current state

- Written to page 0, 1, 2, 8, 4, 5
- Written to page 9, 3, 5

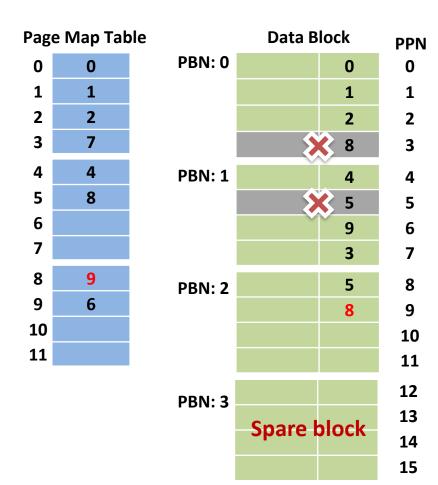
- Write to page 8
- Write to page 9
- Write to page 3
- Write to page I
- Write to page 4



Current state

- Written to page 0, 1, 2, 8, 4, 5
- Written to page 9, 3, 5

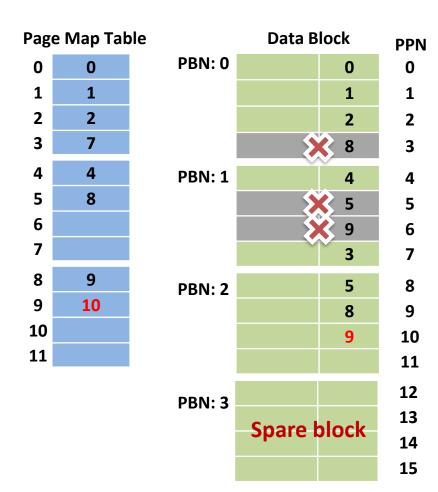
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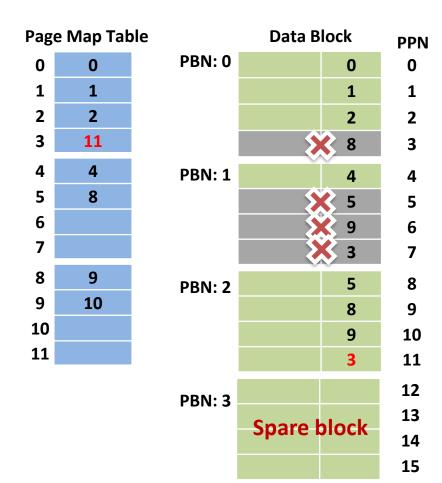
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Current state

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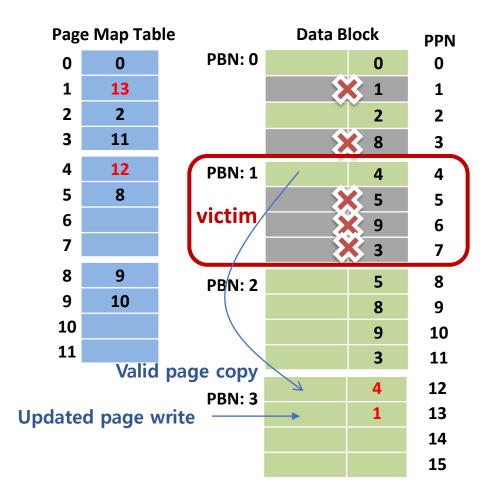
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Current state

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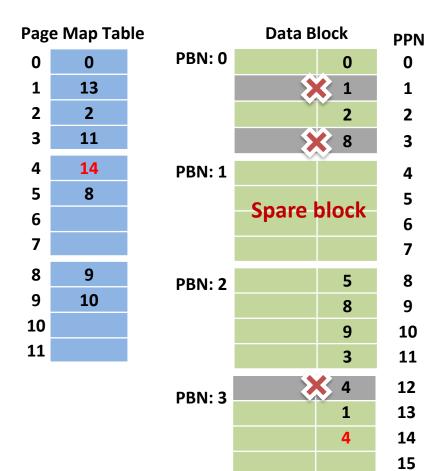
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- Write to page 9
- Write to page 3
- Write to page I
- Write to page 4



Current state

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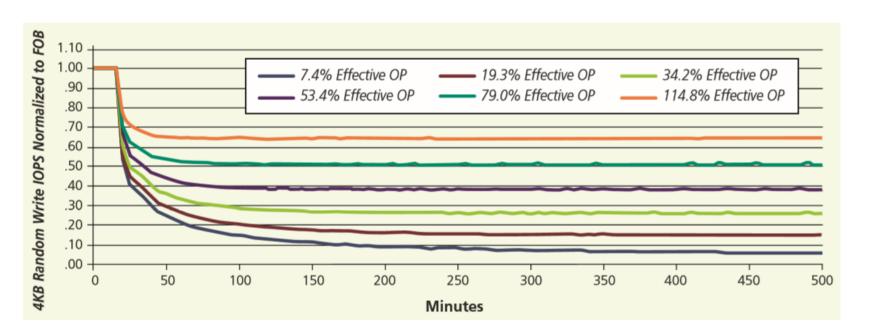
- Write to page 8
- Write to page 9
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- Write to page I
- Write to page 4

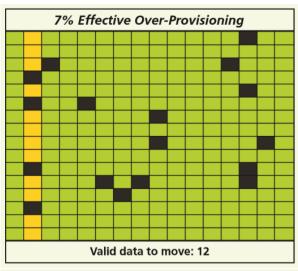


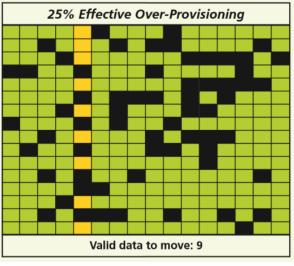
Over-Provisioning and GC

IOPS for random write workloads

- OP (Over-Provisioning) = $\frac{Physical\ Capacity}{Logical\ Capacity} 1$
- What about for sequential write workloads?







Challenges

No in-place update	Address mapping, Garbage collection (with hot/cold separation)				
Limited P/E cycles	Wear leveling				
Bit errors	ECC				
Bad blocks	Bad block remapping				
Read/write disturbance Retention errors	Background activity for data integrity				
Multiple planes/dies/channels	Exploiting parallelism, prefetching				
Slower & more power-consuming program/erase operations	Hiding latency, power throttling				
Sudden power failure	Power loss protection				

OS Implications

- NAND flash has different characteristics compared to disks
 - No seek time
 - Asymmetric read/write access times
 - No in-place-update
 - Good sequential read/write and random read performance, but bad random write performance
 - Wear-leveling
 - •
 - Traditional operating systems have been optimized for disks. What should be changed?

SSD Support in OS & Applications

- Align file system partition with SSD layout
- Larger block size (4KB)
- Turn off "defragmentation" for SSDs
- New "TRIM" command (remove-on-delete)
- Simpler & scalable I/O scheduler
- Flash-aware file systems (e.g., F2FS in Linux/Android)
- New "multi-stream" interface
- User-level storage access (e.g., SPDK)
- Fairness, isolation, etc.

New NVMe SSD Proposals

		Interfaces	Data placement	Flash management	Overwrite	Data movement	Host CPU utilization	Hardware complexity	Computation capability	Software modification
Conventional SSD		Block (SATA, SAS, NVMe)	Host	Device	Yes	-	-	-	No	-
ZNS SSD FDP SSD		Restricted Block (NVMe)	ZNS: Host FDP: Host + Device	ZNS: Host FDP: Host + Device	ZNS: No FDP: Yes	High	High	Low	No	High
KV-SSD		Key-value (NVMe)	Device	Device	Yes	Low	Low	Medium	Some	High
SmartSSD	FPGA	FPGA + Block (NVMe)	Host	Device	Yes	Low	Low	High	Yes	Very High
Computational Storage	7	Compute + Block? (NVMe)	Host or device?	Device	Yes	Low	Low	High	Yes	Very High

Beauty and the Beast

- NAND Flash memory is a beauty
 - Small, light-weight, robust, low-cost, low-power, non-volatile device
- NAND Flash memory is a beast
 - No in-place-update
 - Much slower program/erase operations
 - Erase unit > read/write unit
 - Bit errors
 - Limited lifetime etc.
- Software support is essential for performance and reliability!



